Preferred Device

Complementary Silicon Plastic Power Transistors

TO-220. NPN & PNP Devices

Complementary silicon plastic power transistors are designed for use as high-frequency drivers in audio amplifiers.

Features

- $h_{FE} = 100 \text{ (Min)} @ I_C = 0.5 \text{ Adc}$ $= 10 \text{ (Min)} @ I_C = 2.0 \text{ Adc}$
- Collector-Emitter Sustaining Voltage -V_{CEO(sus)} = 350 Vdc (Min) – MJE15034, MJE15035
- High Current Gain Bandwidth Product $f_T = 30 \text{ MHz (Min)} @ I_C = 500 \text{ mAdc}$
- TO-220AB Compact Package
- Epoxy meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Machine Model: C Human Body Model: 3B
- Pb-Free Packages are Available*

MAXIMUM RATINGS

VCEO(SUS) = 330 $VUC(VIIII) = 10$	/IJL1505-	T, WIJL 15055	
• High Current Gain - Bandwidth Prod	uct		
$f_T = 30 \text{ MHz (Min)} @ I_C = 500$) mAdc		
• TO-220AB Compact Package			
• Epoxy meets UL 94 V-0 @ 0.125 in			36
• ESD Ratings: Machine Model: C			32
Human Body Model:	3B		
• Pb-Free Packages are Available*			
))]	
MAXIMUM RATINGS			
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	350	Vdc
Collector-Base Voltage	V _{CB}	350	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current - Continuous	I _C	4.0	Adc
– Peak		8.0	
Base Current	I _B	1.0	Adc
Total Power Dissipation @ T _C = 25°C	P_{D}	50	W
Derate above 25°C		0.40	W/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2.0 0.016	W W/°C
			
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

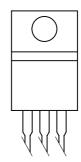
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

4.0 AMPERES POWER TRANSISTORS **COMPLEMENTARY SILICON** 350 VOLTS, 50 WATTS





ORDERING INFORMATION

ONDERING IN ORMATION					
Device	Package	Shipping			
MJE15034	TO-220AB	50 Units / Rail			

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 1)	$(I_C = 10 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	350	-	Vdc
Collector Cutoff Current	$(V_{CB} = 350 \text{ Vdc}, I_{E} = 0)$	I _{CBO}	-	10	μAdc
Emitter Cutoff Current	$(V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0)$	I _{EBO}	-	10	μAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain	$ \begin{aligned} &(I_{C} = 0.1 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \\ &(I_{C} = 0.5 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \\ &(I_{C} = 1.0 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \\ &(I_{C} = 2.0 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \end{aligned} $	h _{FE}	100 100 50 10	- - - -	-
Collector–Emitter Saturation Voltage	$(I_C = 1.0 \text{ Adc}, I_B = 0.1 \text{ Adc})$	V _{CE(sat)}	-	0.5	Vdc
Base-Emitter On Voltage	$(I_C = 1.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc})$	V _{BE(on)}	-	1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain – Bandwidth Product (Note 2) ($I_C = 500 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f_{test} = 1.0 \text{ MHz}$)		f _T	30	_	MHz

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

^{2.} $f_T = |h_{fe}| \cdot f_{test}$.

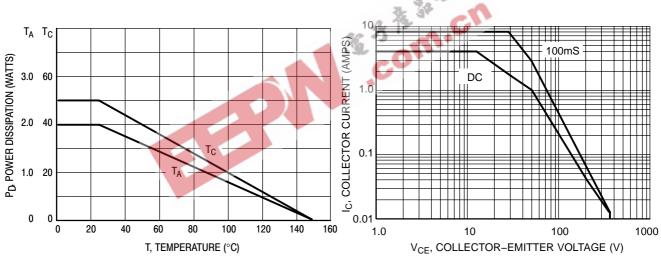


Figure 1. Power Derating

Figure 2. Active Region Safe Operating Area

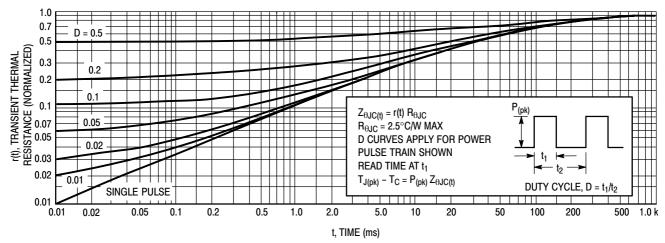


Figure 3. Thermal Response

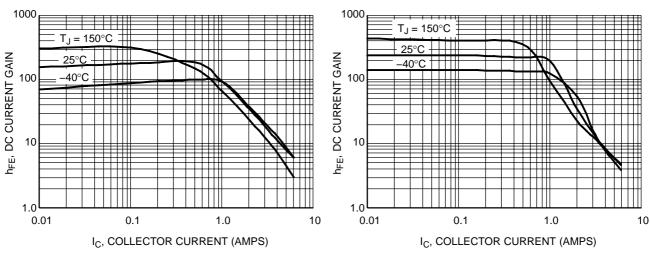


Figure 4. DC Current Gain, V_{CE} = 5.0 V NPN MJE15034

Figure 5. DC Current Gain, V_{CE} = 5.0 V PNP MJE15035

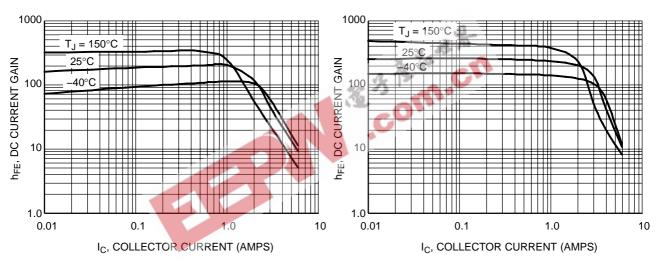


Figure 6. DC Current Gain, V_{CE} = 20 V NPN MJE15034

Figure 7. DC Current Gain, $V_{CE} = 20 \text{ V}$ PNP MJE15035

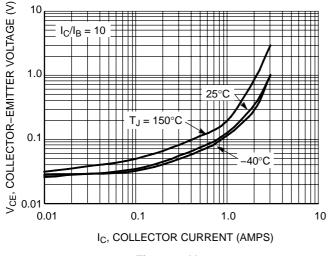


Figure 8. V_{CE(sat)} NPN MJE15034

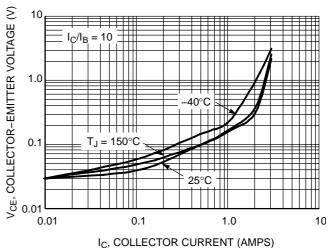
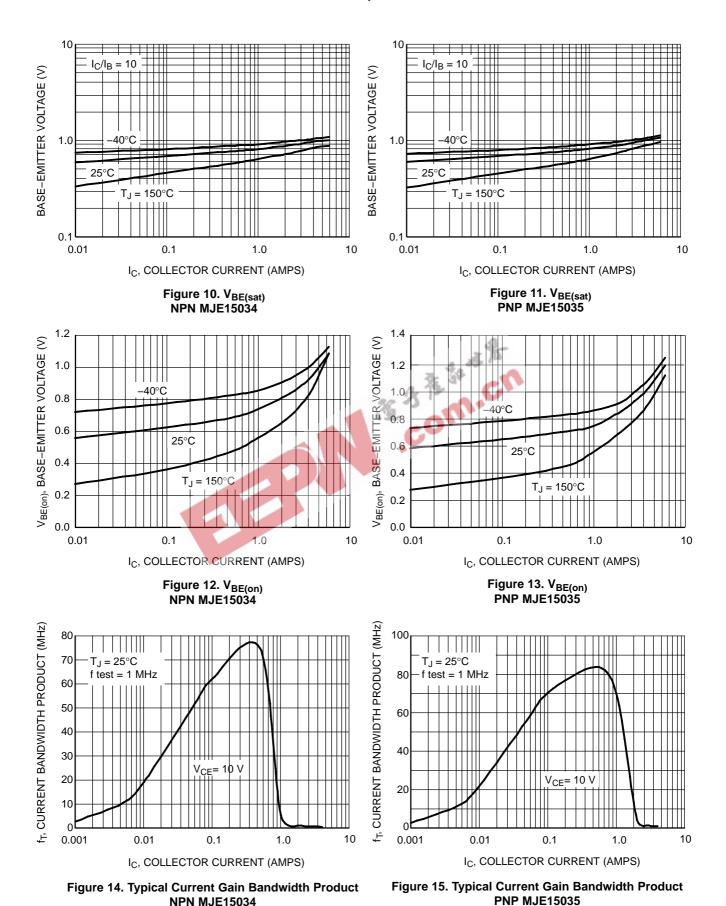


Figure 9. V_{CE(sat)} PNP MJE15035

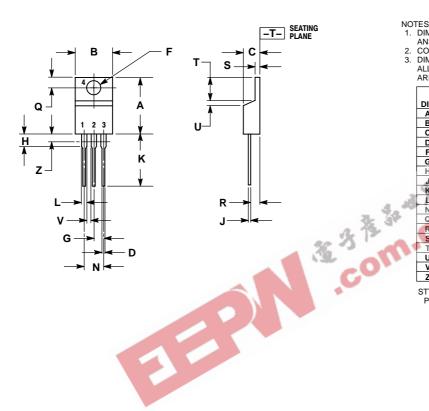


http://onsemi.com

PACKAGE DIMENSIONS

TO-220 THREE-LEAD TO-220AB

CASE 221A-09 **ISSUE AA**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
d	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
_ga	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
T	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
٧	0.045		1.15		
Z		0.080		2.04	

STYLE 1:

- PIN 1. BASE 2. COLLECTOR

 - COLLECTOR

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